

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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UFB200FA40

Ultrafast Soft Recovery Diode

Features

- Fast Recovery Time Characteristic
- Electrically Isolated Base Plate
- Large Creepage Distance Between Terminal
- Simplified Mechanical Designs, Rapid Assembly

 $V_R = 400V$ $V_F(typ.) = 1.0V$ $I_{F(AV)} = 200A$

Description

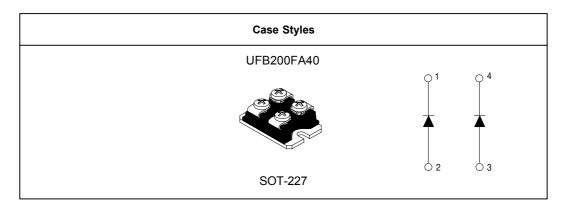
The dual diode series configuration (UFB200FA40) is used for output rectification or frewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, HF welders, motor control and inverters.

Absolute Maximum Ratings

	Parameters		Max	Units
V _R	Cathode-to-Anode Voltage		400	V
lF	Continuous Forward Current, T _C = 100°C	PerLeg	100	А
I _{FSM}	Single Pulse Forward Current, T _C = 25°C	PerLeg	1300	
I _{FRM}	Maximum Repetitive Forward Current	Per Leg	260	
	Max. Power Dissipation, T _C @ 90°C	Per Module	240	W
V _{ISOL}	RMS Isolation Voltage, Any Terminal to Case, t = 1 min		2500	V
T _J , T _{STG}	Operating Junction and Storage Temperature	es	- 55 to 150	℃



Electrical Characteristics $@T_J = 25^{\circ}C$ (unless otherwise specified) per diode

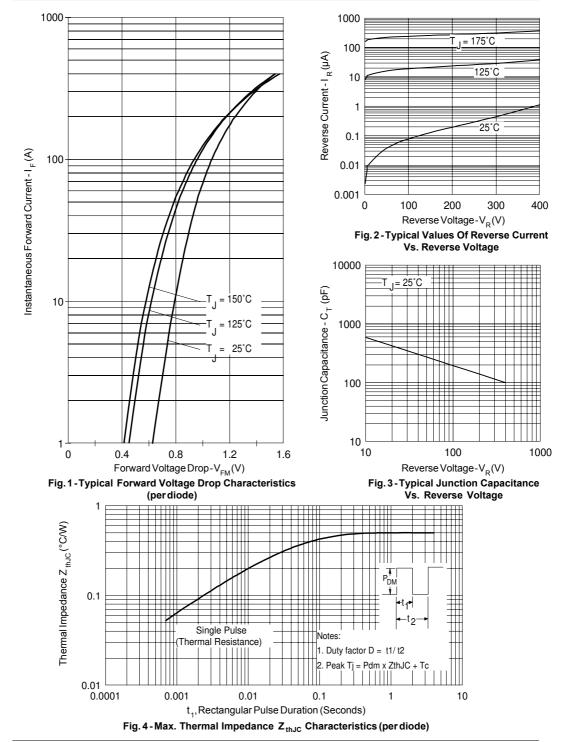
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	Parameters	Min	Тур	Мах	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	400	-	-	V	Ι _R = 100μΑ
V_{FM}	Forward Voltage	-	-	1.2	V	I _F = 100A
		-	-	1.0	V	I _F = 100A, T _J = 150°C
I _{RM}	Reverse Leakage Current	-	-	50	μA	V _R = V _R Rated
		-	-	4	mA	$T_J = 150$ °C, $V_R = V_R$ Rated
Ст	Junction Capacitance	-	100	-	pF	V _R = 400V

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified) per diode

	Parameters	Min	Тур	Max	Units	Test Condition	s
t _{rr}	Reverse Recovery Time	-	-	60	ns	$I_F = 1.0A$, $di_F/dt = 2$	200A/µs, V _R = 30V
		-	93	-		T _J = 25°C	I _F = 150A
		-	172	-		T _J = 125°C	V _R = 200V di _F /dt = 200A/µs
I _{RRM}	Peak Recovery Current	-	11	-	Α	T _J = 25°C	αι _Γ /αι = 200// μ5
		-	20	-		T _J = 125°C	
Q _{rr}	Reverse Recovery Charge	-	490	-	nC	T _J = 25°C	
		-	1740	-		T _J = 125°C	

Thermal - Mechanical Characteristics

	Parameters	Min	Тур	Max	Units
R _{thJC}	Junction to Case, Single Leg Conducting			0.5	°C/W
	Both Leg Conducting			0.25	K/W
R _{thCS}	Case to Heat Sink, Flat, Greased Surface		0.05		
Wt	Weight		30		g
Т	Mounting Torque		1.3		(N*m)



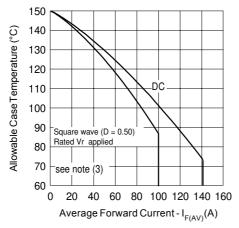


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current (per leg)

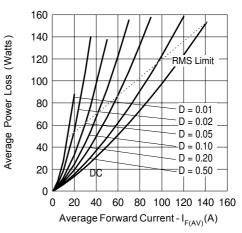


Fig. 6 - Forward Power Loss Characteristics (per leg)

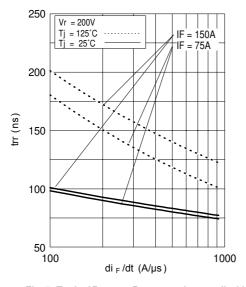


Fig. 7 - Typical Reverse Recovery time vs. di $_{\rm F}$ /dt

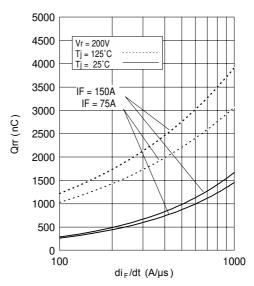


Fig. 8 - Typical Stored Charge vs. di _F /dt

(3) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward Power Loss = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6); $Pd_{REV} = Inverse Power Loss = V_{R1} \times I_{R} (1 - D); I_{R} @ V_{R1} = 80\% rated V_{R}$

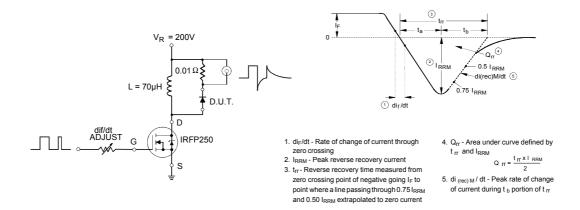
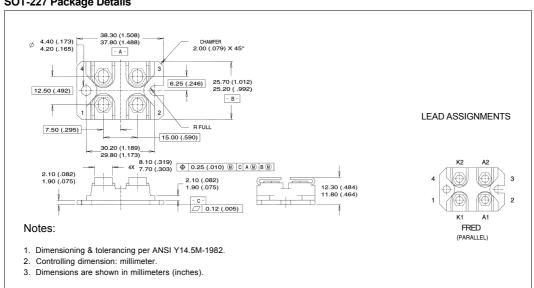


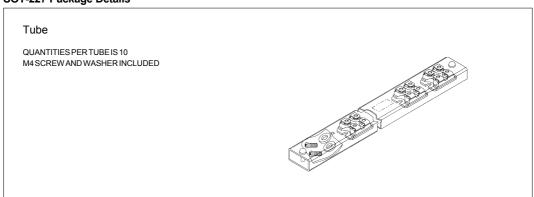
Fig. 1 - Reverse Recovery Parameter Test Circuit

Fig. 2 - Reverse Recovery Waveform and Definitions

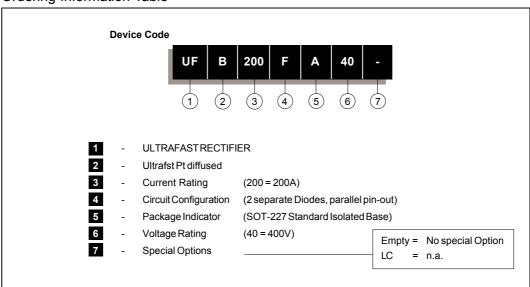
SOT-227 Package Details



SOT-227 Package Details



Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level.

Qualification Standards can be found on IR's Web site.



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